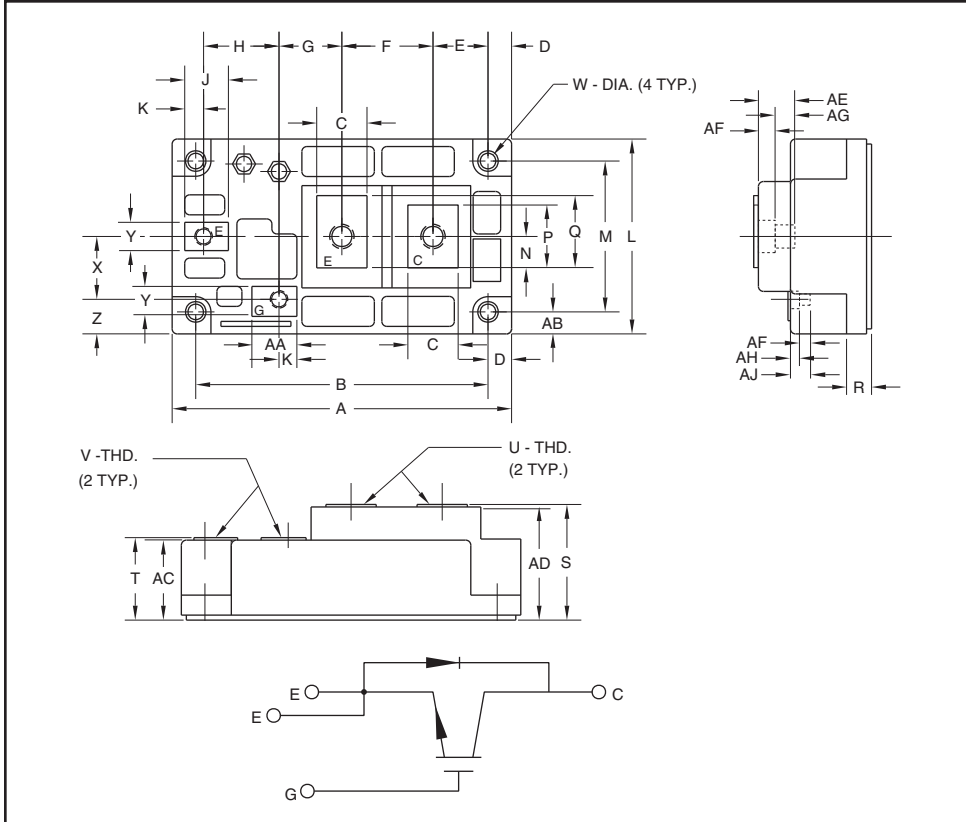


Single IGBT A-Series Module 600 Amperes/1200 Volts



Outline Drawing and Circuit Diagram

Dimensions	Inches	Millimeters
A	4.25	108.0
B	3.66±0.01	93.0±0.25
C	0.63	16.0
D	0.30	7.5
E	0.69	17.5
F	1.14	29.0
G	0.79	20.0
H	0.94	24.0
J	0.55	13.9
K	0.24	6.0
L	2.44	62.0
M	1.89±0.01	48.0±0.25
N	0.39	10.0
P	0.39	20.0
Q	0.51	23.0
R	0.33	8.5
S	1.42+0.04/-0.02	36.0+1/-0.5

Dimensions	Inches	Millimeters
T	1.02+0.04/-0.02	25.8+1/-0.5
U	M6 Metric	M6
V	M4 Metric	M4
W	0.256 Dia.	6.5 Dia.
X	0.79	20.0
Y	0.35	9.0
Z	0.43	11.0
AA	0.53	13.55
AB	0.27	7.0
AC	0.98	25.0
AD	1.38	35.0
AE	0.45	11.5
AF	0.25.0	
AG	0.25	6.5
AH	0.12	3.2
AJ	0.32	8.2



Description:

Powerex IGBT Modules are designed for use in switching applications. Each module consists of one IGBT Transistor in a single configuration with a reverse connected super-fast recovery free-wheel diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

Features:

- ☐ Low Drive Power
- ☐ Low $V_{CE(sat)}$
- ☐ Discrete Super-Fast Recovery Free-Wheel Diode
- ☐ Isolated Baseplate for Easy Heat Sinking

Applications:

- ☐ DC Chopper
- ☐ Inverter
- ☐ UPS
- ☐ Forklift

Ordering Information:

Example: Select the complete part module number you desire from the table below -i.e. CM600HA-24A is a 1200V (V_{CES}), 600 Ampere Single IGBT Power Module.

Type	Current Rating Amperes	V_{CES} Volts (x 50)
CM	600	24

CM600HA-24A
Single IGBT A-Series Module
 600 Amperes/1200 Volts

Maximum Ratings, $T_j = 25^\circ\text{C}$ unless otherwise specified

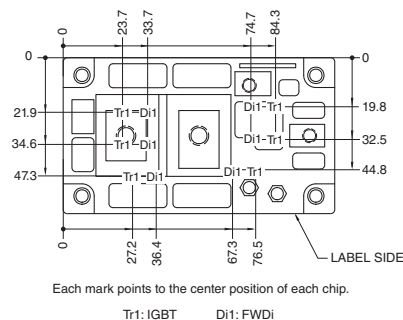
Characteristics	Symbol	Rating	Units
Collector-Emitter Voltage ($V_{GE} = 0\text{V}$)	V_{CES}	1200	Volts
Gate-Emitter Voltage ($V_{CE} = 0\text{V}$)	V_{GES}	± 20	Volts
Collector Current (DC, $T_C = 80^\circ\text{C}$)*2,*4	I_C	600	Amperes
Collector Current (Pulse, Repetitive)*3	I_{CRM}	1200	Amperes
Total Power Dissipation ($T_C = 25^\circ\text{C}$)*2,*4	P_{tot}	3670	Watts
Emitter Current*2	I_E^{*1}	600	Amperes
Emitter Current (Pulse, Repetitive)*3	I_{ERM}^{*1}	1200	Amperes
Isolation Voltage (Charged Part to Baseplate, RMS, $f = 60\text{Hz}$, AC 1 minute)	V_{ISO}	2500	Volts
Junction Temperature	T_j	$-40 \sim +150$	$^\circ\text{C}$
Storage Temperature	T_{stg}	$-40 \sim +125$	$^\circ\text{C}$

*1 Represent ratings and characteristics of the anti-parallel, emitter-to-collector free wheeling diode (FWDi).

*2 The device junction temperature is $T_{j(max)}$ rating (150°C) or less.

*3 Pulse width and repetition rate should be such that device junction temperature (T_j) does not exceed $T_{j(max)}$ rating.

*4 Case temperature (T_C) is measured on the surface of the baseplate just under the chip. Refer to the figure to the right for chip location.



CM600HA-24A
Single IGBT A-Series Module
 600 Amperes/1200 Volts

Electrical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector-Emitter Cutoff Current	I_{CES}	$V_{CE} = V_{CES}, V_{GE} = 0V$	—	—	1.0	mA
Gate-Emitter Leakage Current	I_{GES}	$V_{GE} = V_{GES}, V_{CE} = 0V$	—	—	1.5	μA
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$I_C = 60\text{mA}, V_{CE} = 10V$	6	7	8	Volts
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 600\text{A}, V_{GE} = 15V, T_j = 25^\circ\text{C}^{*5}$	—	2.1	3.0	Volts
		$I_C = 600\text{A}, V_{GE} = 15V, T_j = 125^\circ\text{C}^{*5}$	—	2.4	—	Volts
Forward Transfer Admittance	$ y_{fs} $	$I_C = 600\text{A}, V_{CE} = 10V^{*5}$	180	—	—	S
Input Capacitance	C_{ies}	$V_{CE} = 10V, V_{GE} = 0V$	—	—	105	nF
Output Capacitance	C_{oes}		—	—	9.0	nF
Reverse Transfer Capacitance	C_{res}		—	—	2.0	nF
Gate Charge	Q_G	$V_{CC} = 600V, I_C = 600\text{A}, V_{GE} = 15V$	—	3000	—	nC
Turn-on Delay Time	$t_{d(on)}$	$V_{CC} = 600V, I_C = 600\text{A}, V_{GE} = \pm 15V,$ $R_G = 0.52\Omega, \text{ Inductive Load}$	—	—	660	ns
Rise Time	t_r		—	—	190	ns
Turn-off Delay Time	$t_{d(off)}$		—	—	700	ns
Fall Time	t_f		—	—	350	ns
Emitter-Collector Voltage	V_{EC}^{*1}	$I_E = 600\text{A}, V_{GE} = 0V^{*5}$	—	3.0	3.8	Volts
Reverse Recovery Time	t_{rr}^{*1}	$V_{CC} = 600V, I_E = 600\text{A}, V_{GE} = \pm 15V$	—	—	250	ns
Reverse Recovery Charge	Q_{rr}^{*1}	$R_G = 0.52\Omega, \text{ Inductive Load}$	—	19	—	μC
Internal Gate Resistance	r_g	$T_C = 25^\circ\text{C}$	—	1.0	—	Ω
External Gate Resistance	R_G		0.52	—	7.8	Ω

*1 Represent ratings and characteristics of the anti-parallel, emitter-to-collector free wheeling diode (FWDI).

*5 Pulse width and repetition rate should be such as to cause negligible temperature rise.

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Thermal Resistance Characteristics

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance, Junction to Case	$R_{th(j-c)Q}$	IGBT Part* ⁴	—	—	34	K/kW
Thermal Resistance, Junction to Case	$R_{th(j-c)D}$	FWDi Part* ⁴	—	—	53	K/kW
Contact Thermal Resistance, Case to Heatsink	$R_{th(c-f)}$	Thermal Grease Applied, Per 1 Module* ^{4,7}	—	15	—	K/kW

Mechanical Characteristics

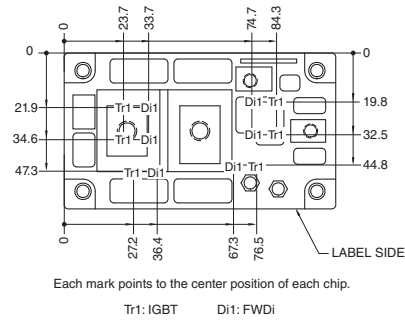
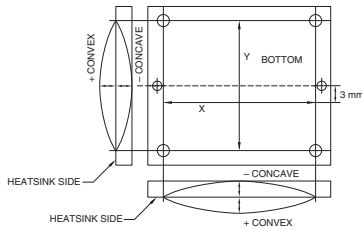
Mounting Torque	M_t	Main Terminal, M6 Screw	17	22	26	in-lb
Mounting Torque	M_t	G/E Auxiliary Terminals	8	10	13	in-lb
Mounting Torque	M_s	Mounting to Heatsink, M6 Screw	22	27	31	in-lb
Weight	m			480		g
Flatness of Baseplate	e_c	On Centerline X, Y* ⁶	±0	—	+100	μm

*⁴ Case temperature (T_C) and heatsink temperature (T_S) is measured on the surface (mounting side) of the baseplate and the heatsink side just under the chips. Refer to the figure to the right for chip location.

The heatsink thermal resistance should be measured just under the chips.

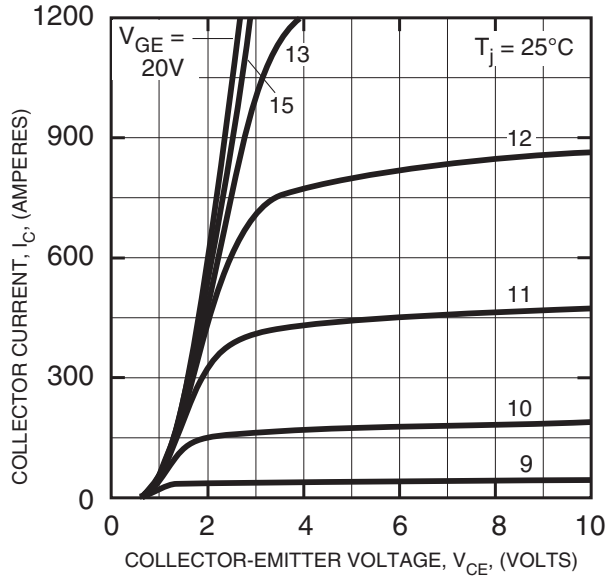
*⁶ Baseplate (mounting side) flatness measurement points (X, Y) are shown in the figure below.

*⁷ Typical value is measured by using thermally conductive grease of $\lambda = 0.9 \text{ [W/(m} \cdot \text{K)]}$.

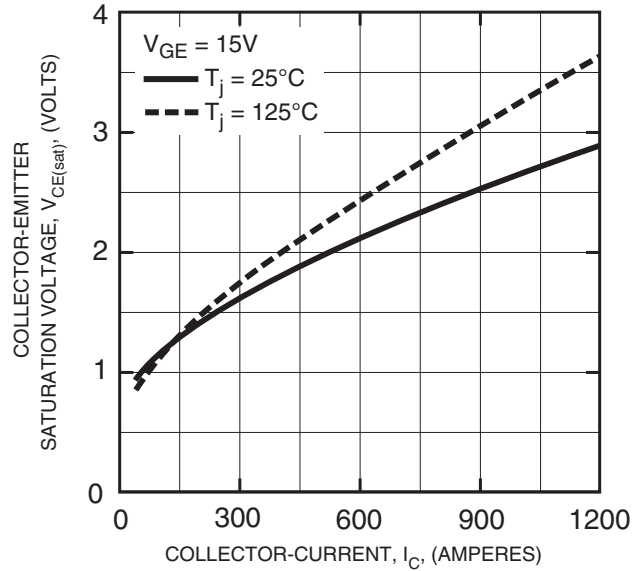


CM600HA-24A
Single IGBT A-Series Module
 600 Amperes/1200 Volts

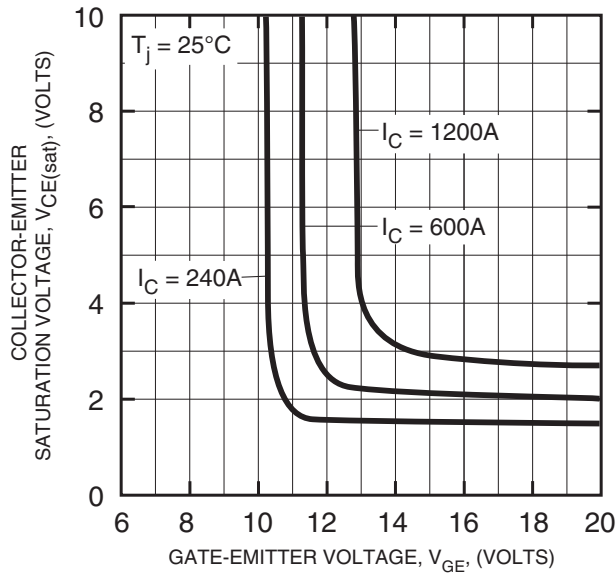
**OUTPUT CHARACTERISTICS
(TYPICAL)**



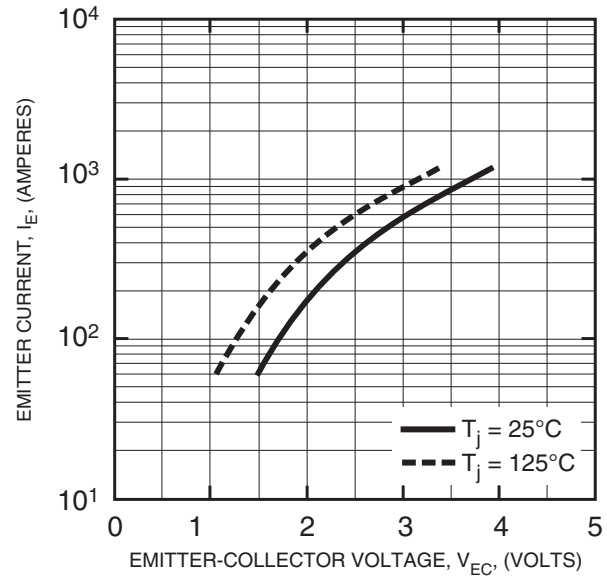
**COLLECTOR-EMITTER
SATURATION VOLTAGE CHARACTERISTICS
(TYPICAL)**



**COLLECTOR-EMITTER
SATURATION VOLTAGE CHARACTERISTICS
(TYPICAL)**

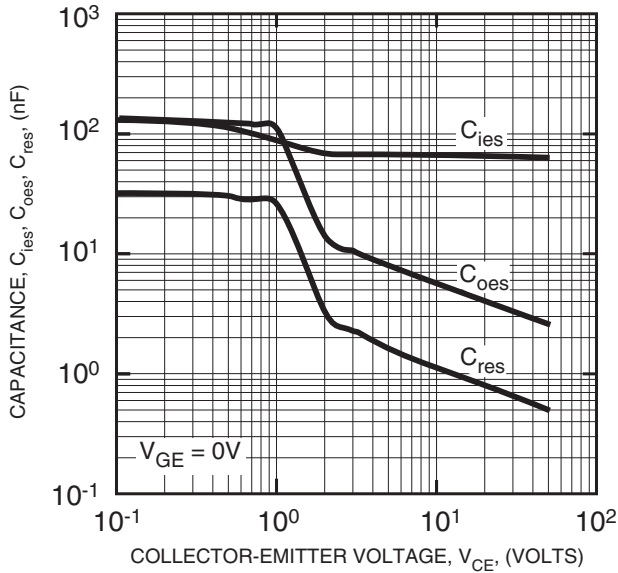


**FREE-WHEEL DIODE
FORWARD CHARACTERISTICS
(TYPICAL)**

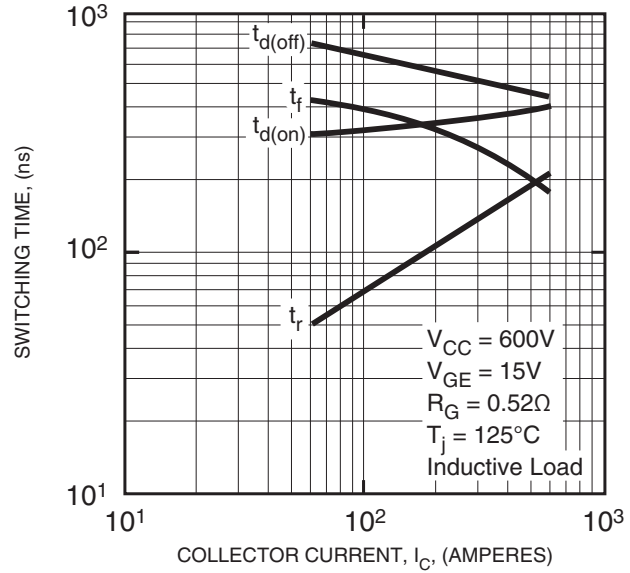


CM600HA-24A
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 600 Amperes/1200 Volts

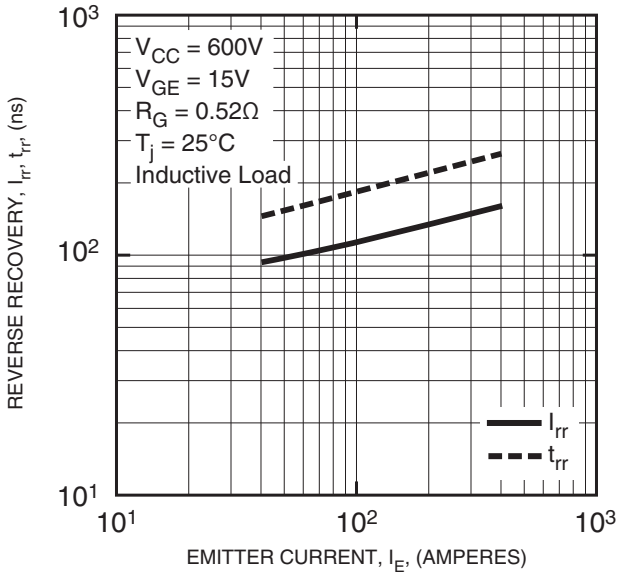
CAPACITANCE VS. V_{CE}
 (TYPICAL)



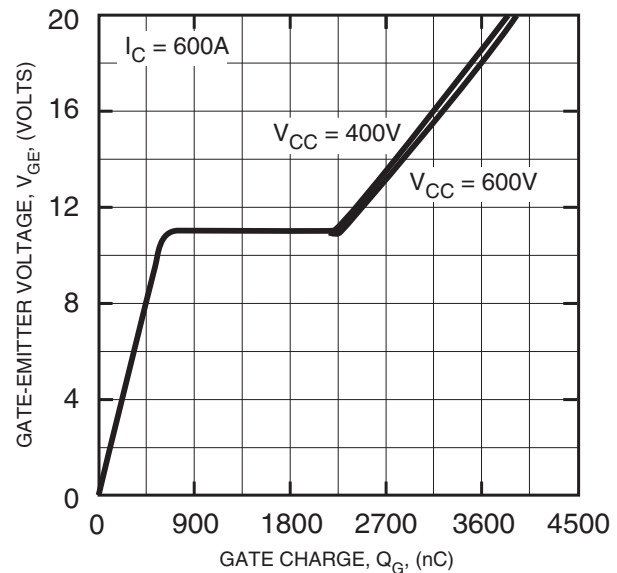
HALF-BRIDGE
SWITCHING CHARACTERISTICS
 (TYPICAL)



REVERSE RECOVERY CHARACTERISTICS
 (TYPICAL)

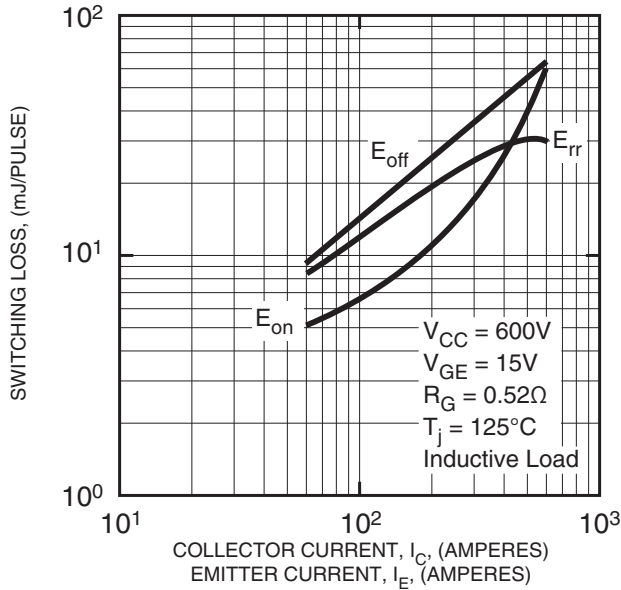


GATE CHARGE VS. V_{GE}

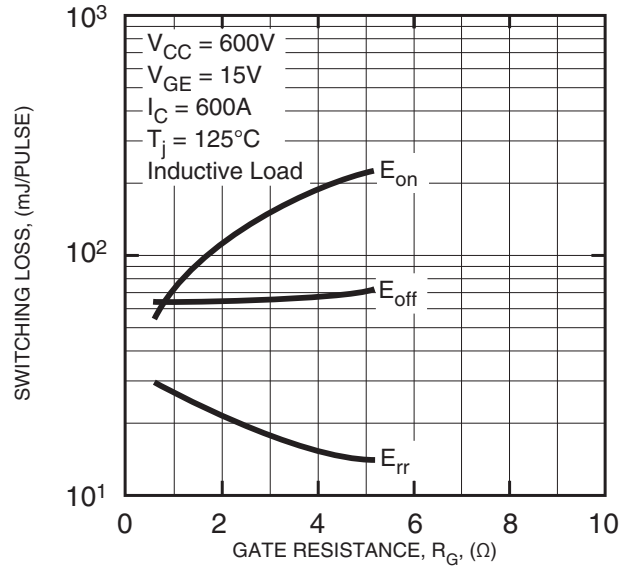


CM600HA-24A
Single IGBT A-Series Module
 600 Amperes/1200 Volts

**SWITCHING LOSS VS. COLLECTOR CURRENT
 (TYPICAL)**



**SWITCHING LOSS VS. GATE RESISTANCE
 (TYPICAL)**



**TRANSIENT THERMAL
 IMPEDANCE CHARACTERISTICS
 (IGBT & FWDi)**

